

ELECTRONIC STRUCTURES WITH REDUCED CAPACITANCE

ABSTRACT OF THE INVENTION

An apparatus and method is described incorporating one or more layers of SiCOH and one or more layers of patterned conductors in an integrated circuit chip. The invention
5 overcomes the problem of capacitance by lowering the k of the dielectric and overcomes the problem of breakdown voltage and the leakage current by tailoring the composition of SiCOH.